

Appl. No. 99/999,999

Claims 1-36 and 39-42 are cancelled; claims 43-45 are added; claims 37-38 and 43-45 are pending in the application. Applicant requests examination of the pending claims.

The added claims 43-45 are fully supported by the specification. With respect to claim 43, support for the claimed subject matter is found in the specification at page 9, lines 13-15. With respect to claim 44, the subject matter claimed is supported by the specification at page 11, lines 3-7. With respect to claim 45, the subject matter claimed is supported by the specification at page 13, lines 11-13.

Respectfully submitted,

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By:

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Priority Application Serial No. .... 09/837,645  
Priority Filing Date .... April 17, 2001  
Inventor .... Sandhu et al.  
Assignee .... Micron Technology, Inc.  
Priority Group Art Unit .... 2813  
Priority Examiner .... Schillinger, L.  
Attorney's Docket No. .... MI22-1780  
Title: Methods of Forming a Thin Film Transistor

VERSION WITH MARKINGS TO SHOW CHANGES MADE ACCOMPANYING  
PRELIMINARY AMENDMENT

In the Specification

The replacement specification paragraphs incorporate the following amendments. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

At p. 1, before the "Technical Field" Section, insert

RELATED PATENT DATA

This patent is a divisional application of U.S. Patent Application Serial No. 09/837,645 which was filed on April 17, 2001, which is a continuation of U.S. Patent No. 6,238,957, issued on May 29, 2001, which is a continuation of U.S. Patent No. 6,001,675, issued on December 14, 1999, which is a continuation of U.S. Patent No. 5,665,611, which was issued on September 9, 1997.

**In the Claims**

The claims have been amended as follows. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

Claims 1-36 and 39-42 are cancelled.

The following claims are added:

43. (New) The method of claim 37 wherein the forming a fluorine containing layer comprises forming a sacrificial fluorine containing layer over the thin film transistor layer by chemical vapor deposition utilizing  $WF_6$  and  $SiH_4$  precursors.

44. (New) The method of claim 43 further comprising after the transferring fluorine, removing the sacrificial layer from over the thin film transistor layer.

45. (New) A method of forming a bottom-gated thin film transistor comprising the following steps:

forming a transistor gate;

forming a polycrystalline thin film transistor layer over the transistor gate;

forming a fluorine containing layer over the polycrystalline thin film transistor layer;

providing a buffering layer intermediate the thin film transistor layer and the fluorine containing layer; and

transferring fluorine into the polycrystalline thin film transistor layer from the fluorine containing layer.

**-END OF DOCUMENT-**